



ORIENT-CHIP

OCM4616S

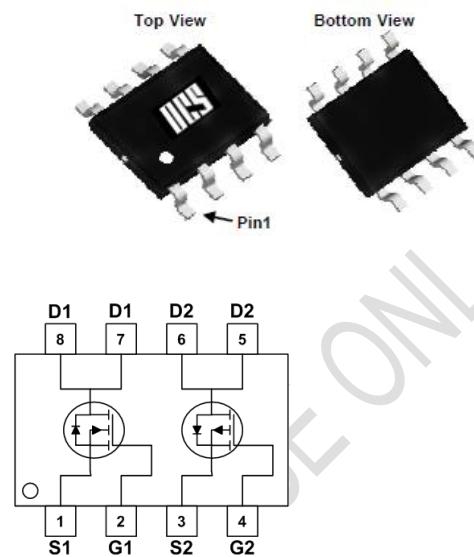
N and P-Channel Enhancement Mode Power MOSFET

## Features

- Trench Technology
- Supper high density cell design
- Fast Switching Extremely Low Threshold Voltage
- 100% Avalanche test
- Pb-free lead plating, RoHS compliant
- Package SOP-8L

## Product Summary

	$BV_{DSS}$	$R_{DS(on)}$ Type	$I_D$ Max
N-CH	30V	18m $\Omega$ @ $V_{GS}=10V$	8A
		25m $\Omega$ @ $V_{GS}=4.5V$	6A
P-CH	-30V	27m $\Omega$ @ $V_{GS}=-10V$	-8A
		38m $\Omega$ @ $V_{GS}=-4.5V$	-6A



## Application

- DC/DC converters
- Power supply converters circuit
- Power Load Switch
- BLDC



## Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	$V_{DS}$	30	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current <sup>1,4</sup>	$I_D$	8	-8	A
		6	-6	
Pulsed Drain Current <sup>2,4</sup>	$I_{DM}$	32	-32	A
Single Pulse Avalanche ( $L=0.5mH$ )	EAS	12	35	mJ
Maximum Power Dissipation <sup>3</sup>	$PD$	2	2	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	-55 To 150	°C

## Thermal Characteristic

Parameter	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient <sup>(Note 1)</sup>	$R_{\theta JA}$	62	°C/W